

## BUR52

### HIGH CURRENT NPN SILICON TRANSISTOR

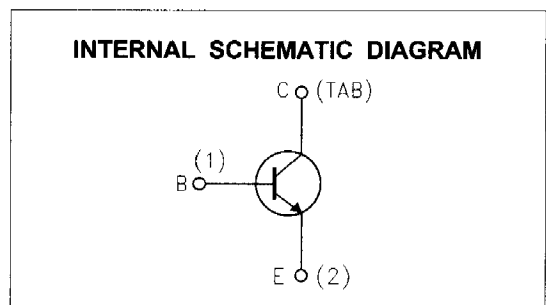
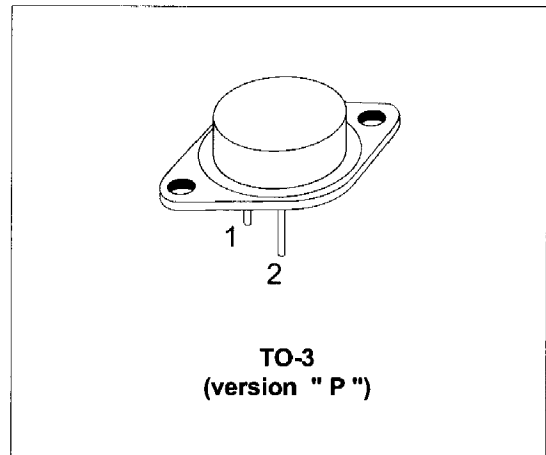
- NPN TRANSISTOR
- MAINTAINS GOOD SWITCHING PERFORMANCE EVEN WITHOUT NEGATIVE BASE DRIVE

#### APPLICATIONS

- LINEAR AND SWITCHING INDUSTRIAL EQUIPMENT

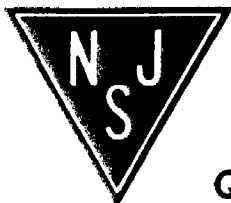
#### DESCRIPTION

The BUR52 is a silicon multiepitaxial planar NPN transistors in modified Jedec TO-3 metal case, intended for use in switching and linear applications in military and industrial equipment.



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	350	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	250	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	10	V
$I_C$	Collector Current	60	A
$I_{CM}$	Collector Peak Current ( $t_p = 10$ ms)	80	A
$I_B$	Base Current	16	A
$P_{tot}$	Total Dissipation at $T_c \leq 25$ °C	350	W
$T_{stg}$	Storage Temperature	-65 to 200	°C
$T_j$	Max. Operating Junction Temperature	200	°C



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**TO-3 (version P) MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.00	11.7	13.10	0.433		0.516
B	1.45	1.5	1.60	0.057		0.063
C	2.7		2.92	0.106		0.115
D	8.9		9.4	0.350		0.370
E	19.00		20.00	0.748		0.787
G	10.70	10.9	11.10	0.421	0.429	0.437
N	16.50	16.9	17.20	0.650	0.665	0.677
P	25.00		26.00	0.984		1.024
R	3.88		4.2	0.153		0.165
U	38.50		39.30	1.516		1.547
V	30.00	30.14	30.30	1.181	1.186	1.193

